

• General Description

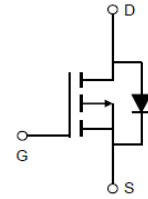
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

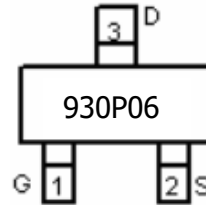
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- BLDC Motor driver

• Product Summary


$V_{DS} = -60V$

$R_{DS(ON)} = 103m\Omega$

$I_D = -1.5A$


SOT23-3
• Ordering Information:

Part NO.	ZM930P06T
Marking	930P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings (T_c =25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	-1.5	A
	$I_D @ T_C = 75^\circ C$	-1.14	A
	$I_D @ T_C = 100^\circ C$	-0.94	A
Pulsed Drain Current ^①	I_{DM}	-4.5	A
Total Power Dissipation ^②	$P_D @ T_C = 25^\circ C$	1.5	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	0.5	W
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy	E_{AS}	10	mJ
ESD Level (HBM)		Class 1B	

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	80	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	250	° C/W
Lead temperature for soldering Purposes(10s)	T _L	-	-	260	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-1.5A		103	120	mΩ
		V _{GS} =-4.5V, I _D =-1A		128	166	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-1A		4		s
Source-drain voltage	V _{SD}	I _S =-1.5A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	650	-	pF
Output capacitance	C _{oss}		-	120	-	
Reverse transfer capacitance	C _{rss}		-	70	-	

•Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} =25V	-	12	-	nC
Gate - Source charge	Q _{gs}	I _D = 1A	-	1.6	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	2.6	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Power Dissipation Derating Curve

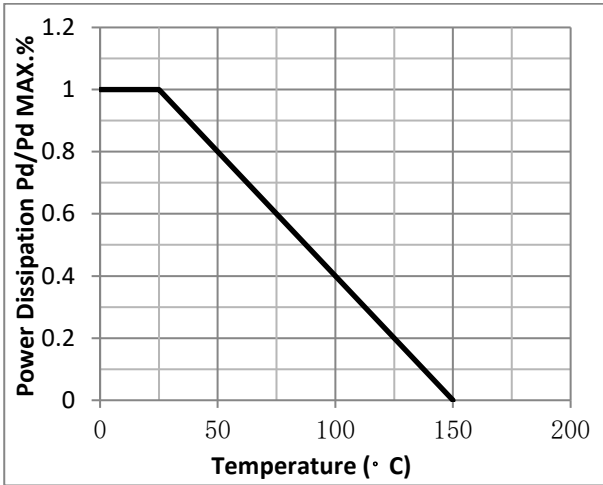


Fig.2 Typical output Characteristics

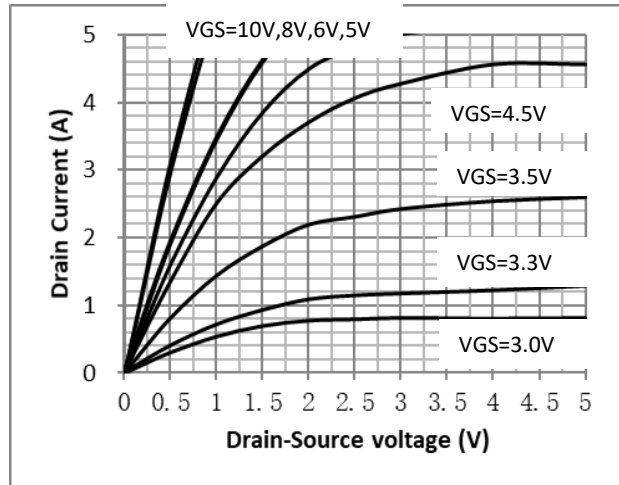


Fig.3 Threshold Voltage V.S Junction Temperature

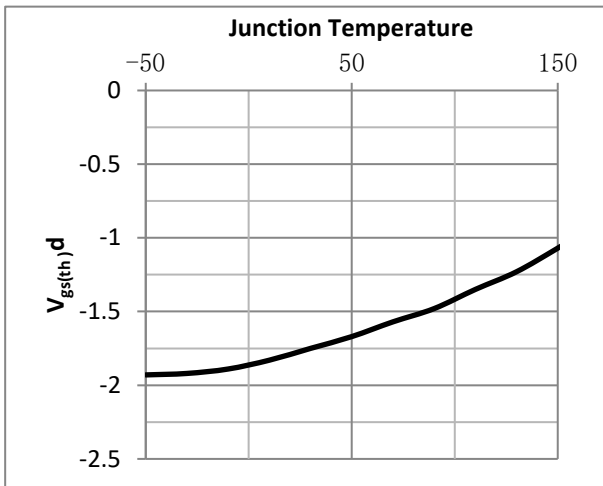


Fig.4 Resistance V.S Drain Current

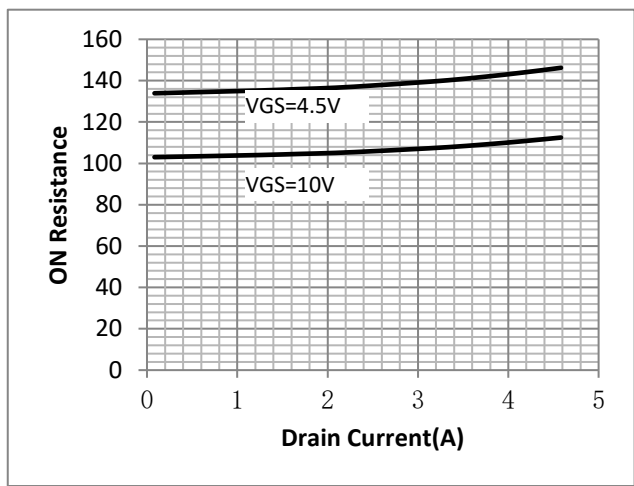


Fig.5 On-Resistance VS Gate Source Voltage

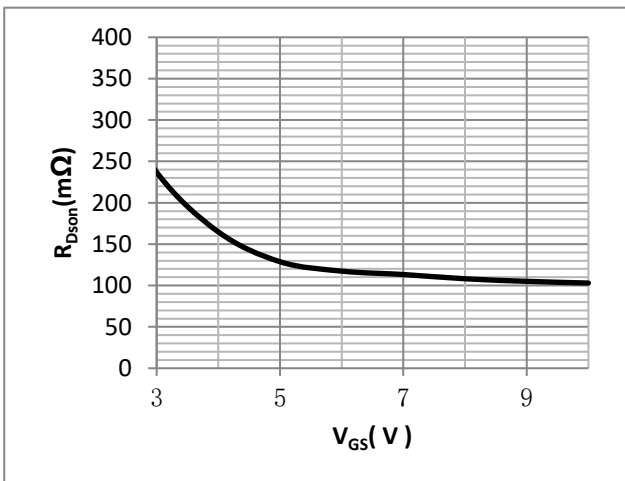


Fig.6 On-Resistance V.S Junction Temperature

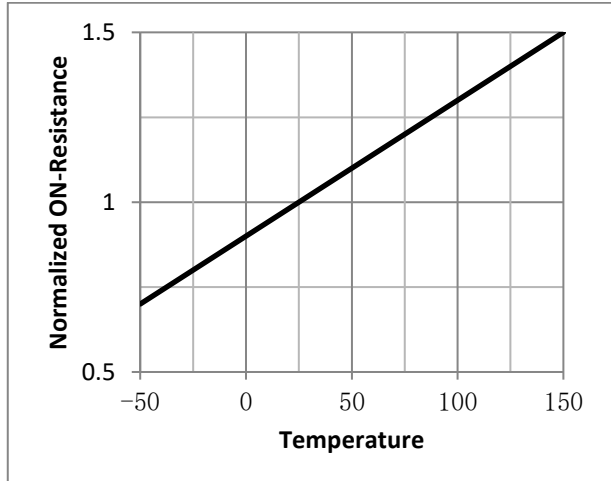


Fig.7 Transfer Characteristics

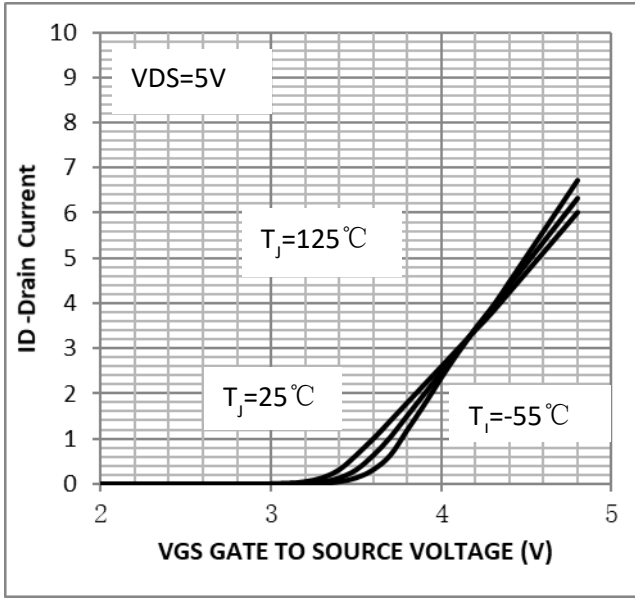


Fig.7 Switching Time Measurement Circuit

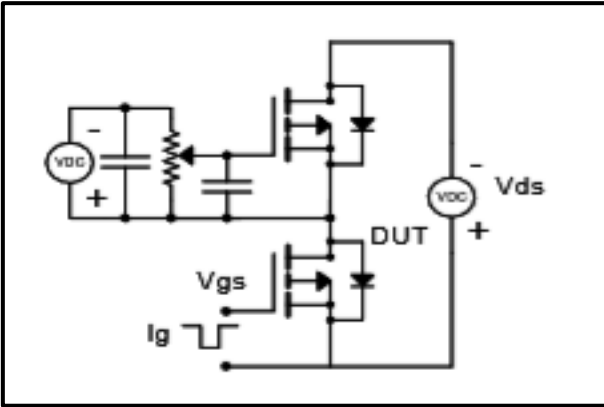


Fig.8 Gate Charge Waveform

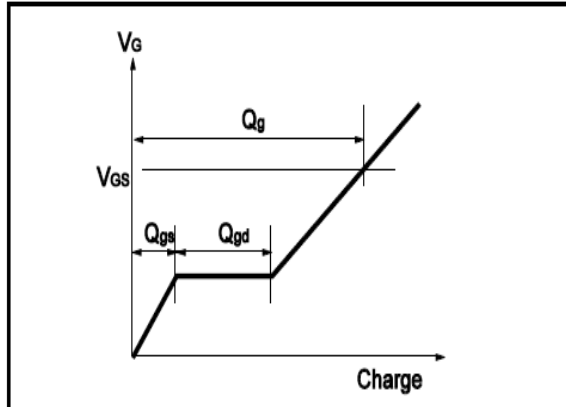


Fig.9 Switching Time Measurement Circuit

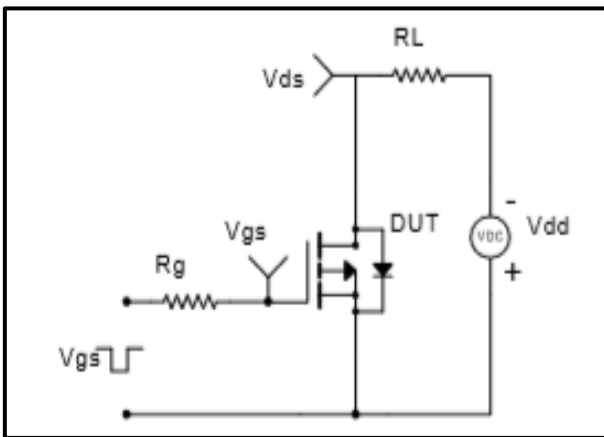


Fig.10 Gate Charge Waveform

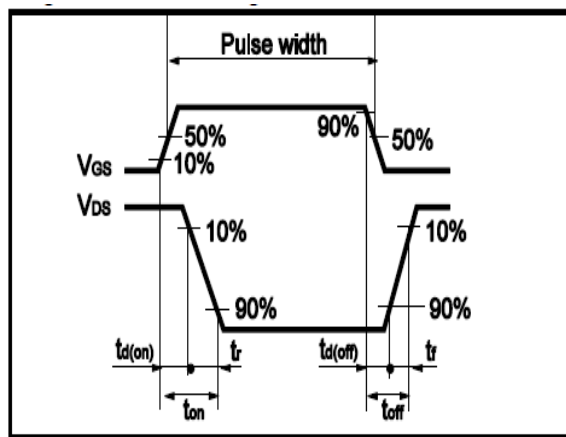


Fig.11 Avalanche Measurement Circuit

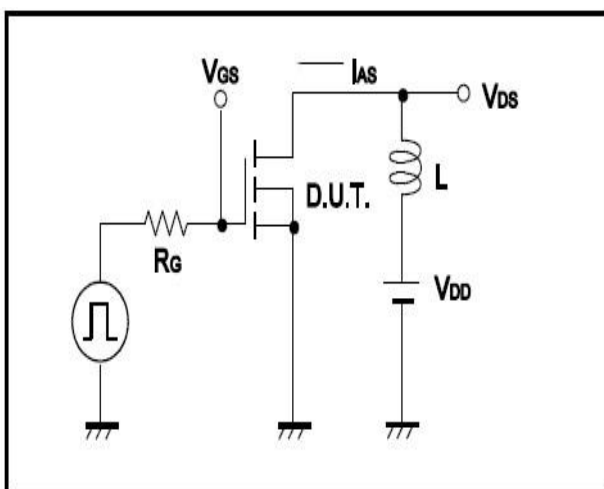
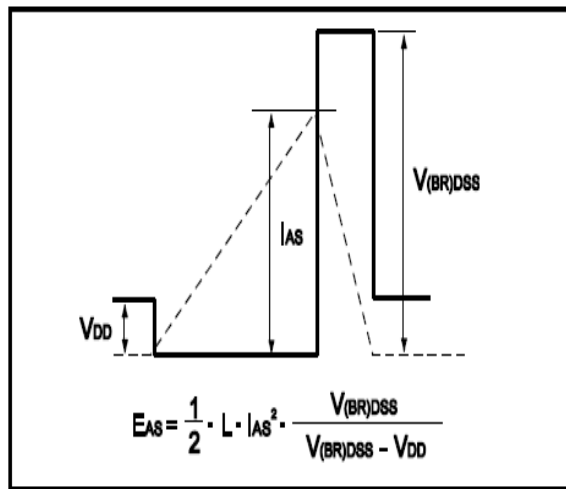
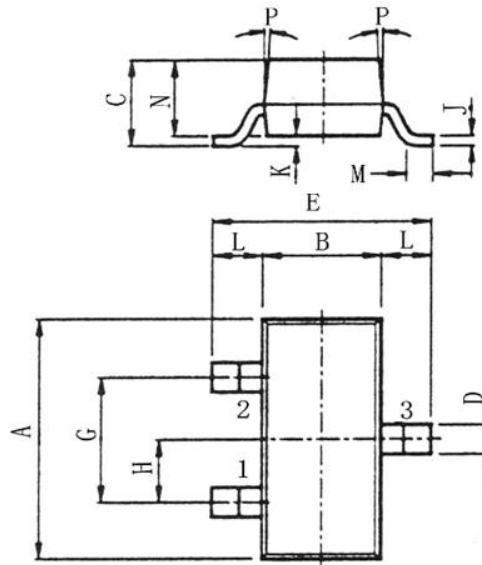


Fig.12 Avalanche Waveform



•Dimensions(SOT23)

Unit: mm



SYMBOL	min	nom	max
A	2.70	2.9	3.10
B	1.15	1.3	1.50
C			1.30
D	0.35	0.4	0.55
E	2.20	2.4	2.70
G	1.70	1.9	2.10
H	0.85	0.95	1.05
J	0.05	0.10	0.20
K	0.00		0.10
L	0.45	0.55	0.65
M	0.20		
N	0.90	1.00	1.20
P		7°	